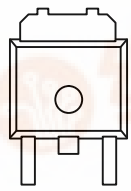


Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

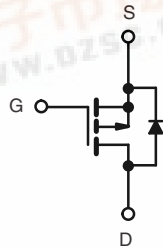
V_{DS} (V)	- 30
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.012
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.029
I_D (A)	- 50
Configuration	Single

TO-252



Top View

Drain Connected to Tab



P-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified^d
- Find out more about Vishay's Automotive Grade Product Requirements at: www.vishay.com/applications



RoHS
COMPLIANT
HALOGEN
FREE

ORDERING INFORMATION

Package	TO-252
Lead (Pb)-free and Halogen-free	SQD45P03-12-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	$\pm$ 20	
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}^a$	I_D	- 50	A
	$T_C = 125\text{ }^{\circ}\text{C}$		- 34	
Continuous Source Current (Diode Conduction) ^a		I_S	- 50	
Pulsed Drain Current ^b		I_{DM}	- 200	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	- 31	
Single Pulse Avalanche Energy		E_{AS}	48	mJ
Maximum Power Dissipation ^b	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	71	W
	$T_C = 125\text{ }^{\circ}\text{C}$		23	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	2.1	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



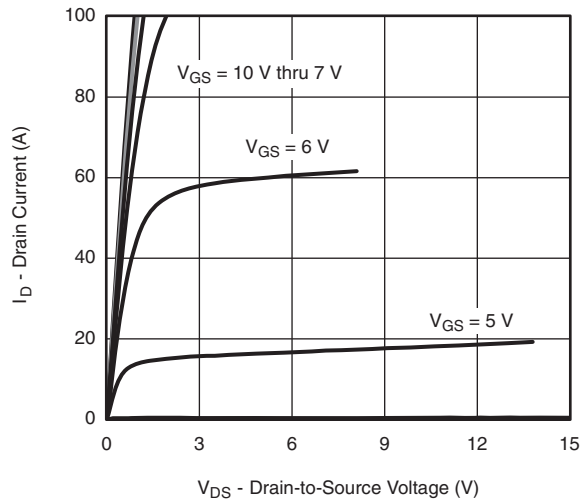
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA		- 30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA		- 1.5	-	- 2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 30 V	-	-	- 1	μA
		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	
		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 50	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 15 A	-	0.008	0.012	Ω
		V _{GS} = - 10 V	I _D = - 15 A, T _J = 125 °C	-	-	0.018	
		V _{GS} = - 10 V	I _D = - 15 A, T _J = 175 °C	-	-	0.020	
		V _{GS} = - 4.5 V	I _D = - 12 A	-	0.019	0.029	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 17 A		-	34	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = - 15 V, f = 1 MHz	-	2794	3495	pF
Output Capacitance	C _{OSS}			-	616	770	
Reverse Transfer Capacitance	C _{rss}			-	470	590	
Total Gate Charge ^c	Q _g	V _{GS} = - 10 V	V _{DS} = - 15 V, I _D = - 45 A	-	55.3	83	nC
Gate-Source Charge ^c	Q _{gs}			-	7.3	11	
Gate-Drain Charge ^c	Q _{gd}			-	14	21	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 15 V, R _L = 0.33 Ω I _D ≅ - 45 A, V _{GEN} = - 10 V, R _g = 1 Ω		-	11	16.5	ns
Rise Time ^c	t _r			-	11	16.5	
Turn-Off Delay Time ^c	t _{d(off)}			-	29	43.5	
Fall Time ^c	t _f			-	19	28.5	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	- 200	A
Forward Voltage	V _{SD}	I _F = - 40 A, V _{GS} = 0 V		-	- 0.9	- 1.5	V

Notes

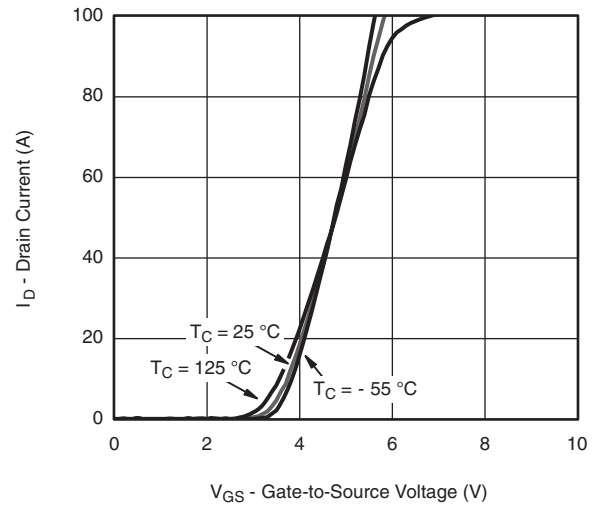
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

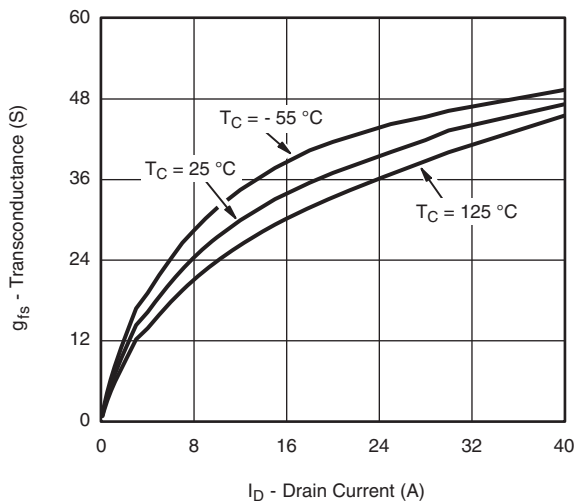
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



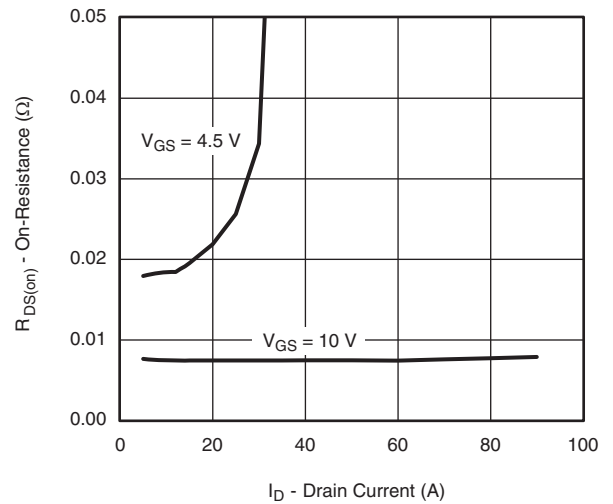
Output Characteristics



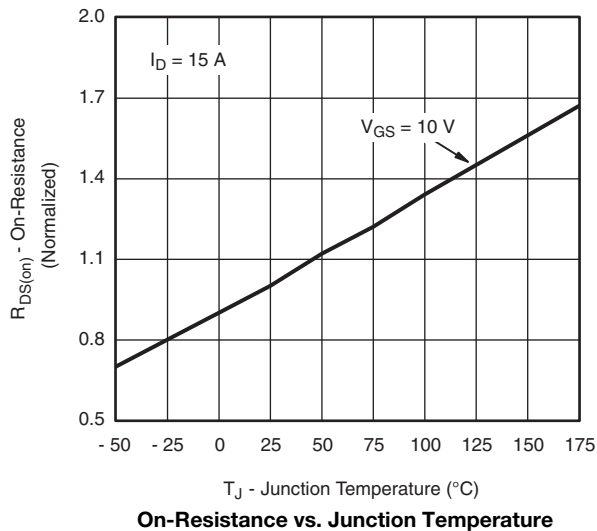
Transfer Characteristics



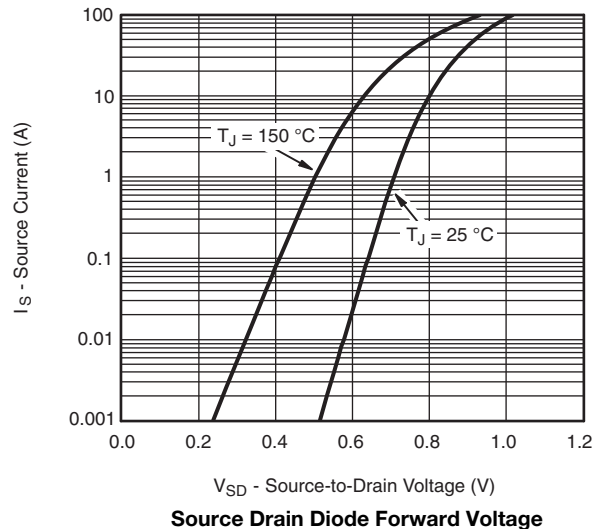
Transconductance



On-Resistance vs. Drain Current

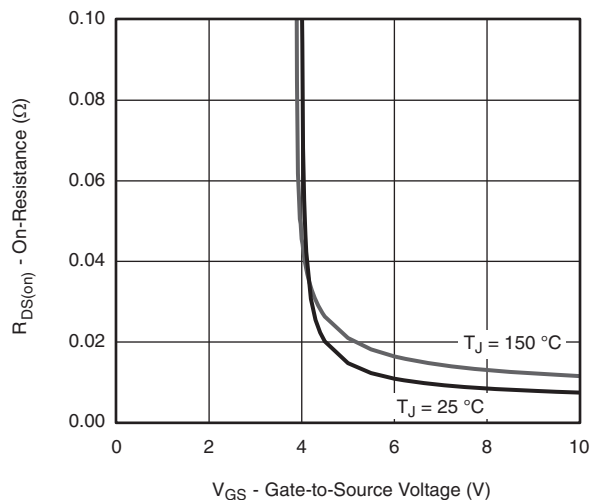


On-Resistance vs. Junction Temperature

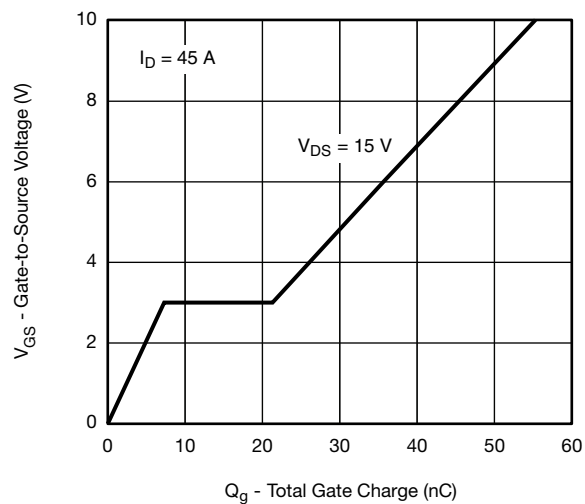


Source Drain Diode Forward Voltage

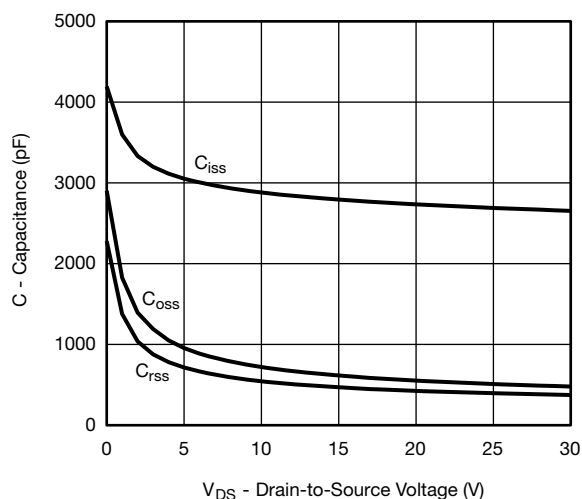
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



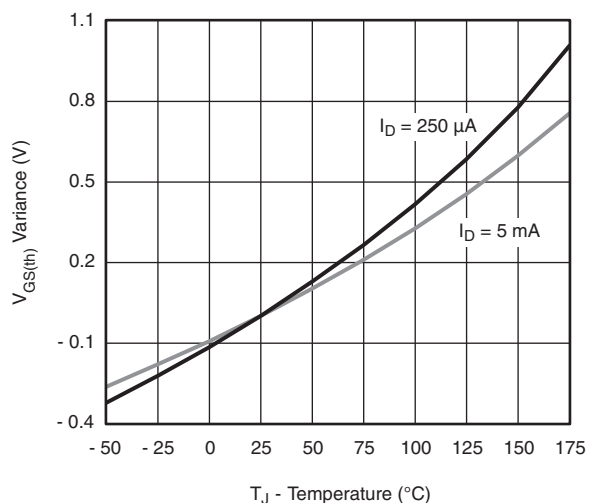
On-Resistance vs. Gate-to-Source Voltage



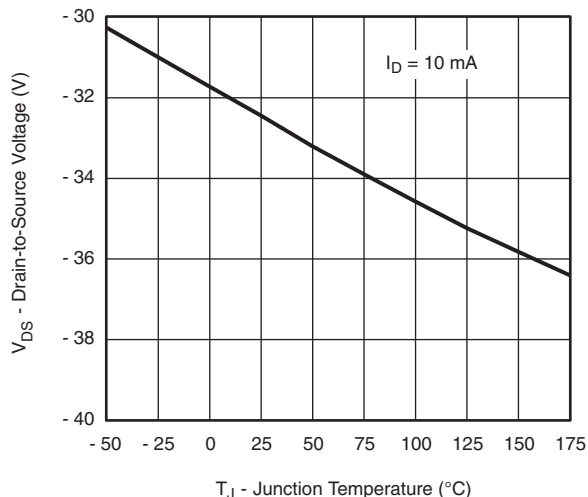
Gate Charge



Capacitance

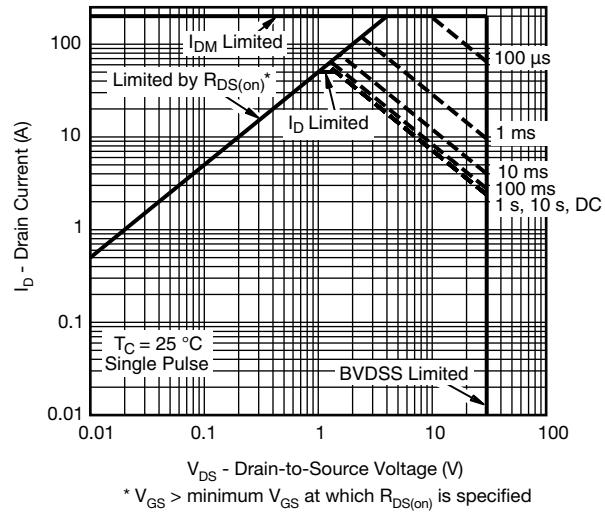


Threshold Voltage

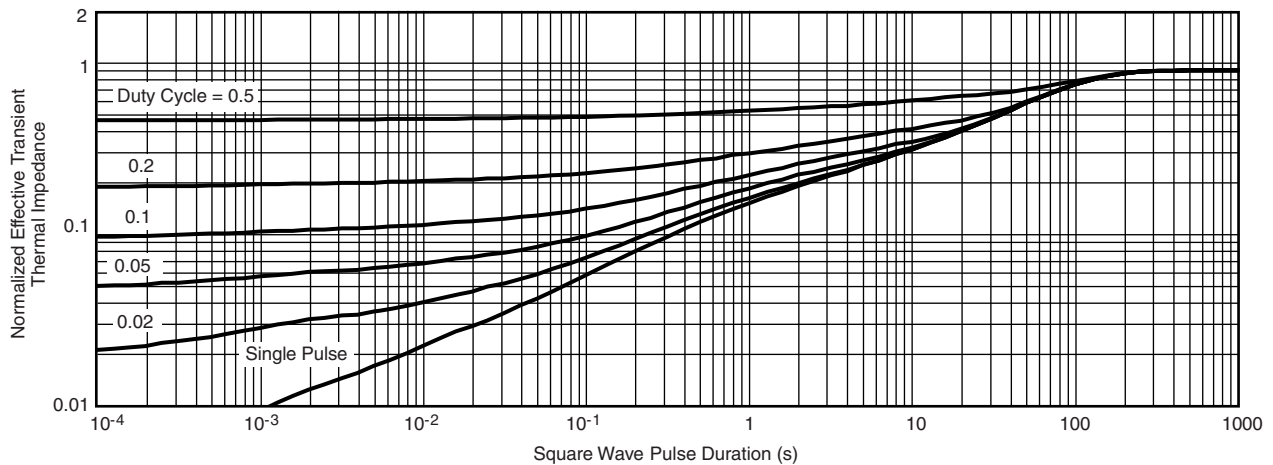


Drain Source Breakdown vs. Junction Temperature

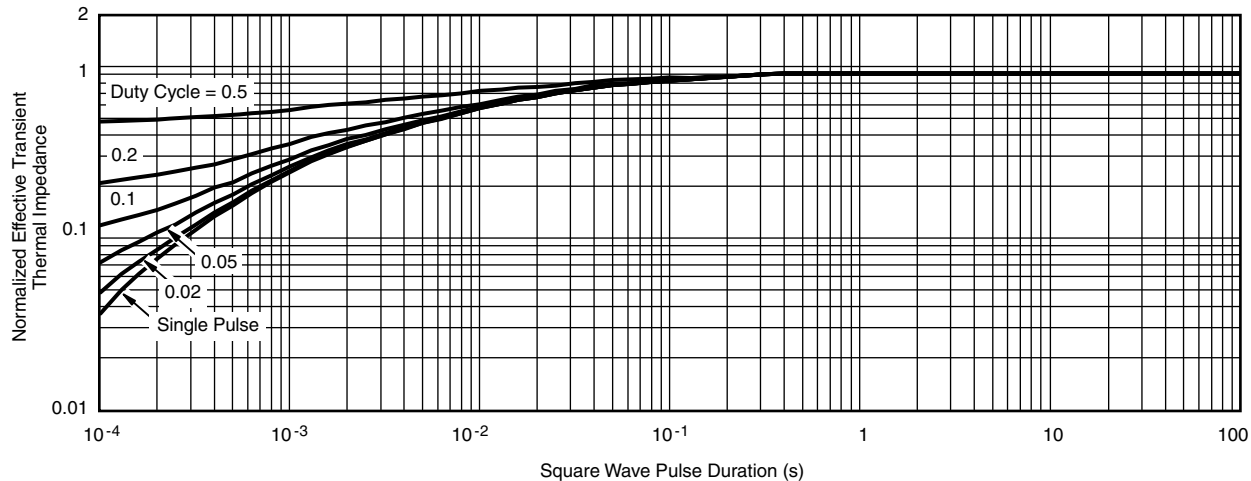
THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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